

Simon Hammersley

List of Publications by Year in descending order

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Version: 2024-02-01

21
papers

347
citations

933264

10
h-index

794469

19
g-index

21
all docs

21
docs citations

21
times ranked

550
citing authors

#	ARTICLE	IF	CITATIONS
1	Carrier dynamics at trench defects in InGaN/GaN quantum wells revealed by time-resolved cathodoluminescence. <i>Nanoscale</i> , 2022, 14, 402-409.	2.8	13
2	GaN surface sputter damage investigated using deep level transient spectroscopy. <i>Materials Science in Semiconductor Processing</i> , 2021, 126, 105654.	1.9	2
3	Effect of Si-doped InGaN underlayers on photoluminescence efficiency and recombination dynamics in InGaN/GaN quantum wells. <i>Journal Physics D: Applied Physics</i> , 2021, 54, 475104.	1.3	2
4	Optical properties of c-Plane InGaN/GaN single quantum wells as a function of total electric field strength. <i>Japanese Journal of Applied Physics</i> , 2019, 58, SCCB09.	0.8	5
5	Optical and structural properties of dislocations in InGaN. <i>Journal of Applied Physics</i> , 2019, 125, .	1.1	11
6	Effect of stacking faults on the photoluminescence spectrum of zincblende GaN. <i>Journal of Applied Physics</i> , 2018, 123, .	1.1	10
7	Photoluminescence studies of cubic GaN epilayers. <i>Physica Status Solidi (B): Basic Research</i> , 2017, 254, 1600733.	0.7	16
8	Comparative studies of efficiency droop in polar and non-polar InGaN quantum wells. <i>Applied Physics Letters</i> , 2016, 108, .	1.5	18
9	A comparison of the optical properties of InGaN/GaN multiple quantum well structures grown with and without Si-doped InGaN prelayers. <i>Journal of Applied Physics</i> , 2016, 119, .	1.1	13
10	Diatom Frustules as a Biomineralized Scaffold for the Growth of Molybdenum Disulfide Nanosheets. <i>Chemistry of Materials</i> , 2016, 28, 5582-5586.	3.2	13
11	Effect of QW growth temperature on the optical properties of blue and green InGaN/GaN QW structures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2016, 13, 209-213.	0.8	5
12	Room temperature PL efficiency of InGaN/GaN quantum well structures with prelayers as a function of number of quantum wells. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2016, 13, 248-251.	0.8	7
13	Effect of electron blocking layers on the conduction and valence band profiles of InGaN/GaN LEDs. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2016, 13, 262-265.	0.8	1
14	Effects of quantum well growth temperature on the recombination efficiency of InGaN/GaN multiple quantum wells that emit in the green and blue spectral regions. <i>Applied Physics Letters</i> , 2015, 107, .	1.5	58
15	Supplemental Blue LED Lighting Array to Improve the Signal Quality in Hyperspectral Imaging of Plants. <i>Sensors</i> , 2015, 15, 12834-12840.	2.1	24
16	Investigation of unintentional indium incorporation into GaN barriers of InGaN/GaN quantum well structures. <i>Physica Status Solidi (B): Basic Research</i> , 2015, 252, 928-935.	0.7	15
17	Carrier distributions in InGaN/GaN light-emitting diodes. <i>Physica Status Solidi (B): Basic Research</i> , 2015, 252, 890-894.	0.7	6
18	On the origin of blue-green emission from heteroepitaxial nonpolar a-plane InGaN quantum wells. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012, 9, 465-468.	0.8	4

#	ARTICLE	IF	CITATIONS
19	The consequences of high injected carrier densities on carrier localization and efficiency droop in InGaN/GaN quantum well structures. <i>Journal of Applied Physics</i> , 2012, 111, .	1.1	105
20	Study of efficiency droop and carrier localisation in an InGaN/GaN quantum well structure. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011, 8, 2194-2196.	0.8	16
21	Carrier dynamics in non-polar GaN/AlGaIn quantum wells intersected by basal-plane stacking faults. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010, 7, 1894-1896.	0.8	3